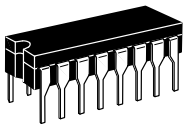
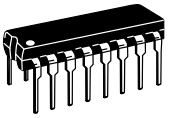
MC14531B

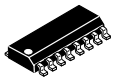
12-Bit Parity Tree



L SUFFIX
CERAMIC
CASE 620



P SUFFIX
PLASTIC
CASE 648



D SUFFIX
SOIC
CASE 751B

ORDERING INFORMATION

MC14XXXBCP	Plastic
MC14XXXBCL	Ceramic
MC14XXXBD	SOIC

T_A = – 55° to 125°C for all packages.

The MC14531B 12–bit parity tree is constructed with MOS P–channel and N–channel enhancement mode devices in a single monolithic structure. The circuit consists of 12 data–bit inputs (D0 thru D11), and even or odd parity selection input (W) and an output (Q). The parity selection input can be considered as an additional bit. Words of less than 13 bits can generate an even or odd parity output if the remaining inputs are selected to contain an even or odd number of ones, respectively. Words of greater than 12–bits can be accommodated by cascading other MC14531B devices by using the W input. Applications include checking or including a redundant (parity) bit to a word for error detection/correction systems, controller for remote digital sensors or switches (digital event detection/correction), or as a multiple input summer without carries.

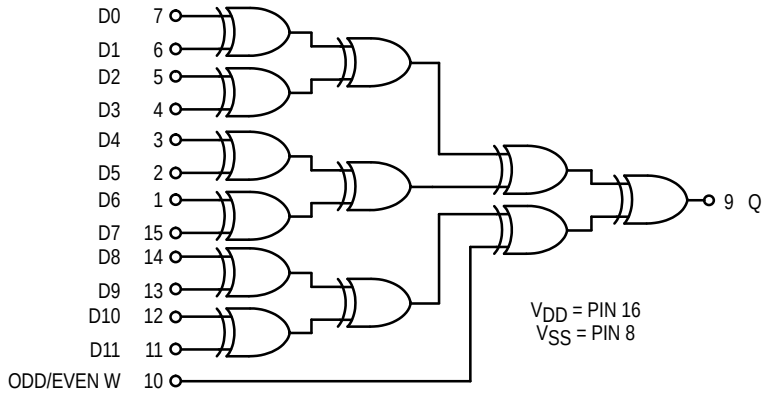
- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- All Outputs Buffered
- Capable of Driving Two Low–Power TTL Loads or One Low–Power Schottky TTL Load Over the Rated Temperature Range
- Variable Word Length
- Diode Protection on All Inputs

MAXIMUM RATINGS* (Voltages Referenced to V_{SS})

Symbol	Parameter	Value	Unit
V_{DD}	DC Supply Voltage	– 0.5 to + 18.0	V
V_{in}, V_{out}	Input or Output Voltage (DC or Transient)	– 0.5 to V_{DD} + 0.5	V
I_{in}, I_{out}	Input or Output Current (DC or Transient), per Pin	± 10	mA
P_D	Power Dissipation, per Package†	500	mW
T_{stg}	Storage Temperature	– 65 to + 150	°C
T_L	Lead Temperature (8–Second Soldering)	260	°C

* Maximum Ratings are those values beyond which damage to the device may occur.
†Temperature Derating:
Plastic “P and D/DW” Packages: – 7.0 mW/°C From 65°C To 125°C
Ceramic “L” Packages: – 12 mW/°C From 100°C To 125°C

LOGIC DIAGRAM



$Q = D0 \oplus D1 \oplus D2 \oplus \cdots \oplus D11 \oplus W$

TRUTH TABLE

Inputs								Output
W	D11	D10	…	D2	D1	D0	Decimal (Octal) Equivalent	Q*
0	0	0	…	0	0	0	0 (0)	0
0	0	0	…	0	0	1	1 (1)	1
0	0	0	…	0	1	0	2 (2)	1
0	0	0	…	0	1	1	3 (3)	0
0	0	0	…	1	0	0	4 (4)	1
0	0	0	…	1	0	1	5 (5)	0
0	0	0	…	1	1	0	6 (6)	0
0	0	0	…	1	1	1	7 (7)	1
*	*	*	*	*	*	*	*	*
*	*	*	…	*	*	*	*	*
*	*	*	*	*	*	*	*	*
1	1	1.	…	0	0	0	8184 (17770)	0
1	1	1	…	0	0	1	8185 (17771)	1
1	1	1	…	0	1	0	8186 (17772)	1
1	1	1	…	0	1	1	8187 (17773)	0
1	1	1	…	1	0	0	8188 (17774)	1
1	1	1	…	1	0	1	8189 (17775)	0
1	1	1	…	1	1	0	8190 (17776)	0
1	1	1	…	1	1	1	8191 (17777)	1

*0 = Even Parity 1 = Odd Parity
NOTE: May redefine to suit application by manipulating W and/or other available D's.

REV 3
1/94

ELECTRICAL CHARACTERISTICS (Voltages Referenced to V_{SS})

Characteristic	Symbol	V_{DD} Vdc	– 55°C		25°C			125°C		Unit
			Min	Max	Min	Typ #	Max	Min	Max	
Output Voltage "0" Level V_{in} = V_{DD} or 0	V_{OL}	5.0	—	0.05	—	0	0.05	—	0.05	Vdc
		10	—	0.05	—	0	0.05	—	0.05	
		15	—	0.05	—	0	0.05	—	0.05	
"1" Level V_{in} = 0 or V_{DD}	V_{OH}	5.0	4.95	—	4.95	5.0	—	4.95	—	Vdc
		10	9.95	—	9.95	10	—	9.95	—	
		15	14.95	—	14.95	15	—	14.95	—	
Input Voltage "0" Level	V_{IL}									Vdc
(V_O = 4.5 or 0.5 Vdc)		5.0	—	1.5	—	2.25	1.5	—	1.5	
(V_O = 9.0 or 1.0 Vdc)		10	—	3.0	—	4.50	3.0	—	3.0	
(V_O = 13.5 or 1.5 Vdc)		15	—	4.0	—	6.75	4.0	—	4.0	
"1" Level	V_{IH}									Vdc
(V_O = 0.5 or 4.5 Vdc)		5.0	3.5	—	3.5	2.75	—	3.5	—	
(V_O = 1.0 or 9.0 Vdc)		10	7.0	—	7.0	5.50	—	7.0	—	
(V_O = 1.5 or 13.5 Vdc)		15	11	—	11	8.25	—	11	—	
Output Drive Current	I_{OH}									mAdc
(V_{OH} = 2.5 Vdc) Source		5.0	– 3.0	—	– 2.4	– 4.2	—	– 1.7	—	
(V_{OH} = 4.6 Vdc)		5.0	– 0.64	—	– 0.51	– 0.88	—	– 0.36	—	
(V_{OH} = 9.5 Vdc)		10	– 1.6	—	– 1.3	– 2.25	—	– 0.9	—	
(V_{OH} = 13.5 Vdc)		15	– 4.2	—	– 3.4	– 8.8	—	– 2.4	—	
(V_{OL} = 0.4 Vdc) Sink	I_{OL}	5.0	0.64	—	0.51	0.88	—	0.36	—	mAdc
(V_{OL} = 0.5 Vdc)		10	1.6	—	1.3	2.25	—	0.9	—	
(V_{OL} = 1.5 Vdc)		15	4.2	—	3.4	8.8	—	2.4	—	
Input Current	I_{in}	15	—	± 0.1	—	±0.00001	± 0.1	—	± 1.0	µAdc
Input Capacitance (V_{in} = 0)	C_{in}	—	—	—	—	5.0	7.5	—	—	pF
Quiescent Current (Per Package)	I_{DD}	5.0	—	5.0	—	0.005	5.0	—	150	µAdc
		10	—	10	—	0.010	10	—	300	
		15	—	20	—	0.015	20	—	600	
Total Supply Current**† (Dynamic plus Quiescent, Per Package) (C_L = 50 pF on all outputs, all buffers switching)	I_T	5.0	I_T = (0.25 µA/kHz) f + I_{DD}							µAdc
		10	I_T = (0.50 µA/kHz) f + I_{DD}							
		15	I_T = (0.75 µA/kHz) f + I_{DD}							

#Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

** The formulas given are for the typical characteristics only at 25°C.

†To calculate total supply current at loads other than 50 pF:

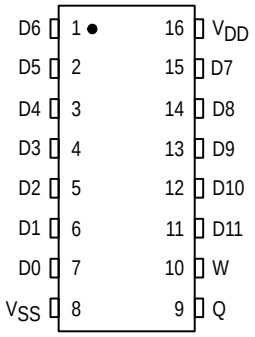
$$I_T(C_L) = I_T(50\ pF) + (C_L - 50)\ Vfk$$

where: I_T is in µA (per package), C_L in pF, V = (V_{DD} – V_{SS}) in volts, f in kHz is input frequency, and k = 0.001.

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $V_{SS} \le (V_{in}$ or $V_{out}) \le V_{DD}$.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.

PIN ASSIGNMENT



SWITCHING CHARACTERISTICS* (C_L = 50 pF, T_A = 25°C)

Characteristic	Symbol	V_{DD}	Min	Typ #	Max	Unit
Output Rise and Fall Time	t_{TLH},					ns
t_{TLH}, t_{THL} = (1.6 ns/pF) C_L + 25 ns	t_{THL}	5.0	—	100	200	
t_{TLH}, t_{THL} = (0.75 ns/pF) C_L + 12.5 ns		10	—	50	100	
t_{TLH}, t_{THL} = (0.55 ns/pF) C_L + 9.5 ns		15	—	40	80	
Propagation Delay Time	t_{PLH},					ns
Data to Q	t_{PHL}					
t_{PLH}, t_{PHL} = (1.7 ns/pF) C_L + 355 ns		5.0	—	440	1320	
t_{PLH}, t_{PHL} = (0.66 ns/pF) C_L + 142 ns		10	—	175	525	
t_{PLH}, t_{PHL} = (0.5 ns/pF) C_L + 95 ns		15	—	120	360	
Odd/Even to Q						
t_{PLH}, t_{PHL} = (1.7 ns/pF) C_L + 165 ns		5.0	—	250	750	
t_{PLH}, t_{PHL} = (0.66 ns/pF) C_L + 67 ns		10	—	100	300	
t_{PLH}, t_{PHL} = (0.5 ns/pF) C_L + 45 ns		15	—	70	210	

* The formulas given are for the typical characteristics only at 25°C.
#Data labelled “Typ” is not to be used for design purposes but is intended as an indication of the IC’s potential performance.

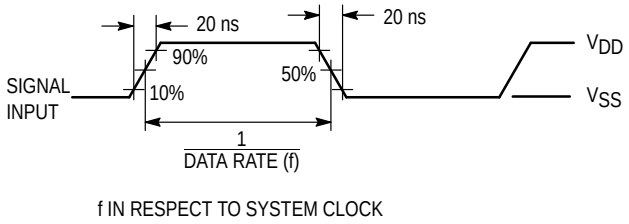


Figure 1. Dynamic Power Dissipation Signal Waveform

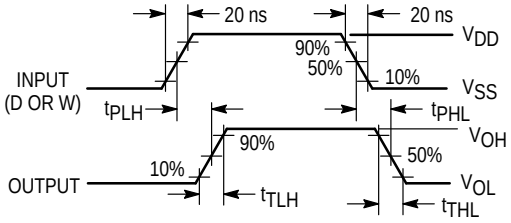
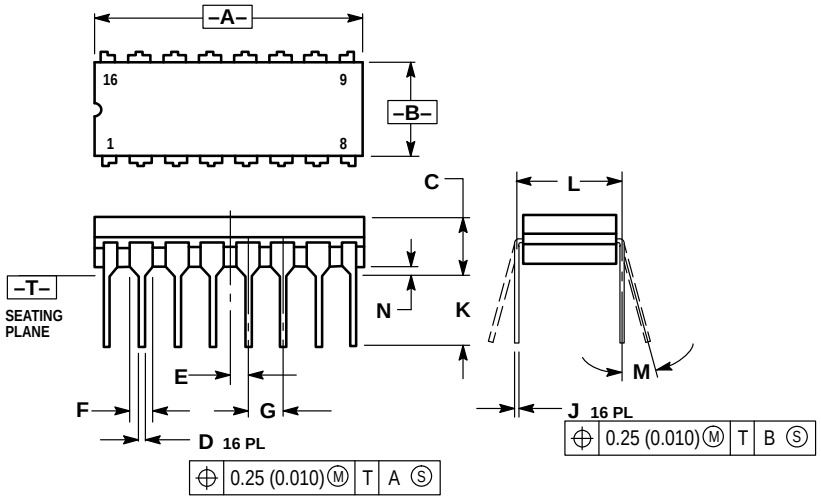


Figure 2. Dynamic Signal Waveforms

OUTLINE DIMENSIONS

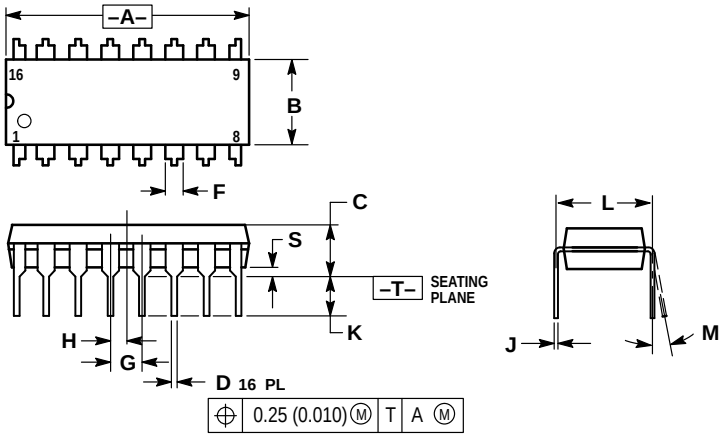
L SUFFIX
CERAMIC DIP PACKAGE
CASE 620–10
ISSUE V



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
4. DIMENSION F MAY NARROW TO 0.76 (0.030) WHERE THE LEAD ENTERS THE CERAMIC BODY.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.750	0.785	19.05	19.93
B	0.240	0.295	6.10	7.49
C	—	0.200	—	5.08
D	0.015	0.020	0.39	0.50
E	0.050 BSC		1.27 BSC	
F	0.055	0.065	1.40	1.65
G	0.100 BSC		2.54 BSC	
H	0.008	0.015	0.21	0.38
K	0.125	0.170	3.18	4.31
L	0.300 BSC		7.62 BSC	
M	0 °	15 °	0 °	15 °
N	0.020	0.040	0.51	1.01

P SUFFIX
PLASTIC DIP PACKAGE
CASE 648–08
ISSUE R

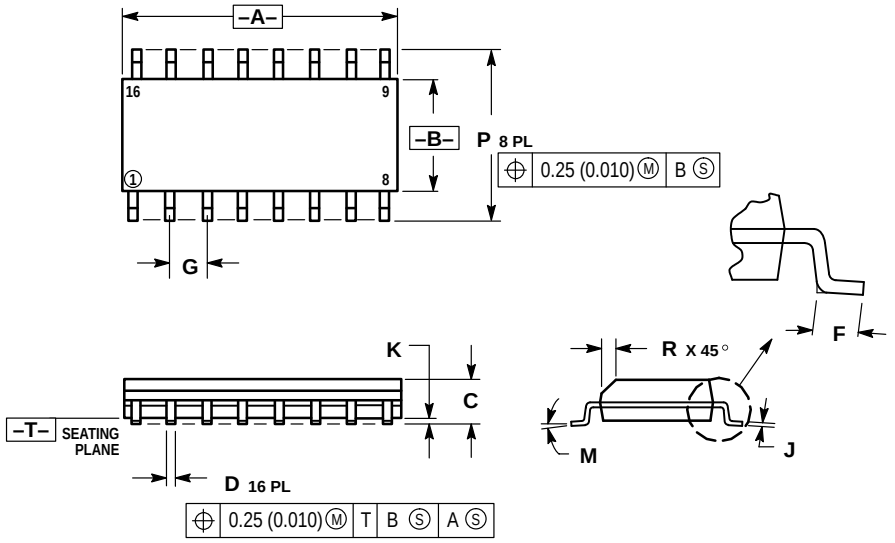


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
5. ROUNDED CORNERS OPTIONAL.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.740	0.770	18.80	19.55
B	0.250	0.270	6.35	6.85
C	0.145	0.175	3.69	4.44
D	0.015	0.021	0.39	0.53
F	0.040	0.70	1.02	1.77
G	0.100 BSC		2.54 BSC	
H	0.050 BSC		1.27 BSC	
J	0.008	0.015	0.21	0.38
K	0.110	0.130	2.80	3.30
L	0.295	0.305	7.50	7.74
M	0 °	10 °	0 °	10 °
S	0.020	0.040	0.51	1.01

OUTLINE DIMENSIONS

D SUFFIX
PLASTIC SOIC PACKAGE
CASE 751B–05
ISSUE J



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	9.80	10.00	0.386	0.393
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

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